

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2003-068987

(43)Date of publication of application : 07.03.2003

(51)Int.Cl.

H01L 27/105

(21)Application number : 2001-257532

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(22)Date of filing : 28.08.2001

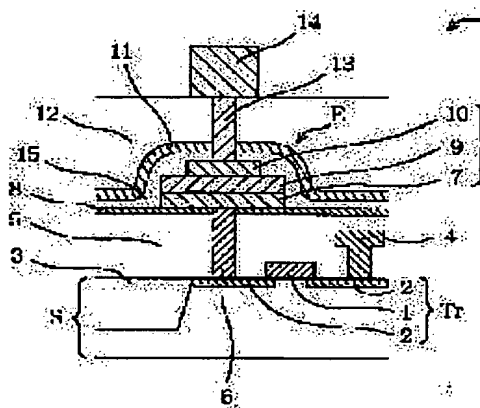
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(54) SEMICONDUCTOR STORAGE DEVICE AND ITS MANUFACTURING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor device having a memory cell capacitor in which a deterioration of characteristics due to a hydrogen or a reducible atmosphere is suppressed and prevented and which has excellent reliability.

SOLUTION: The memory cell capacitor C comprises a lower electrode 7 formed on a first hydrogen barrier film 8, a capacity insulating film 9 made of a ferroelectric material formed on the electrode 7, and an upper electrode 10 formed on the film 9. An interlayer film 15 is formed on the film 8 and the capacitor C so as to cover the capacitor C. The film 15 alleviates a stepwise difference of an edge E of the capacitor. A second hydrogen barrier film 11 is formed on the film 15, and a second insulating film 12 is further formed on the film 11.



LEGAL STATUS

[Date of request for examination]

03.08.2004

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision
of rejection]

[Date of requesting appeal against examiner's
decision of rejection]

[Date of extinction of right]

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